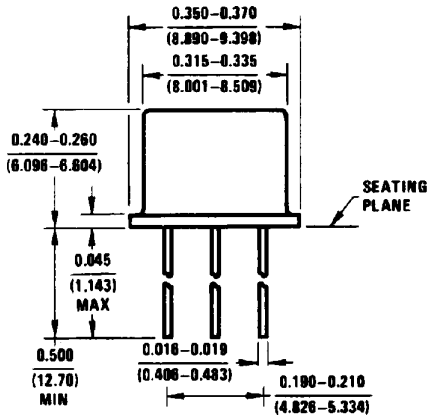
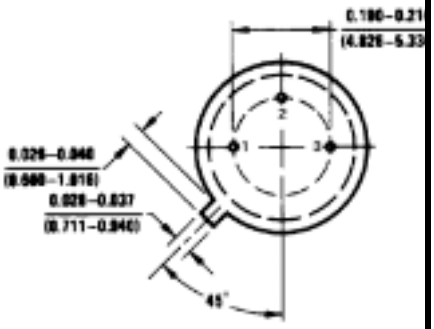
SILICON NPN RF POWER TRANSISTOR

DESCRIPTION: The **MRF237** is designed for large signal power amplifier applications operating to 225 MHz

PACKAGE STYLE TO-39





1 = EMITTER 2 = BASE
3 = COLLECTOR

MAXIMUM RATINGS

I_C	1.0 A
V_{CBO}	36 V
V_{CEO}	18 V
P_{DISS}	8.0 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	22 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 10 mA	18			V
BV_{CES}	I_C = 5.0 mA	36			V
BV_{EBO}	I_C = 1.0 mA	4.0			V
I_{CBO}	V_{CE} = 15 V			.25	mA
h_{FE}	V_{CE} = 5.0 V I_C = 250 mA	5.0			---
C_{OB}	V_{CB} = 15 V f = 1.0 MHz		15	20	pF
G_{PE}	V_{CC} = 12.5 V P_{OUT} = 4.0 W f = 175 MHz	12	14		dB
η		50	62		%

Specifications are subject to change without notice.